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Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



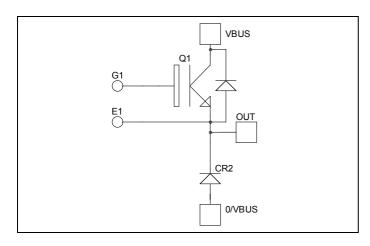






Buck chopper NPT IGBT Power Module





O/VBUS

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration



- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

VBUS

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_{C}	Continuous Collector Current	$T_c = 25$ °C	430	
	Continuous Conector Current	$T_c = 80$ °C	350	A
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	1225	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	1562	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150$ °C	800A @ 600V	

OUT

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Ţ	Zara Cata Valtaga Callacter Current	$V_{GE} = 0V$	$T_j = 25$ °C			200	^
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 600V$	$T_j = 125$ °C			1750	μΑ
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		2.0	2.5	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_C = 360A$ $T_j = 125^{\circ}C$	$T_j = 125$ °C		2.2		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$		3		5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				±300	nA

Dynamic Characteristics

•	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			17.2		nF
C_{oes}	Output Capacitance				1.88		
C_{res}	Reverse Transfer Capacitance				1.6		
Q_g	Total gate Charge	$V_{GE} = 15V$			1320		
Q_{ge}	Gate – Emitter Charge	$V_{Bus} = 300V$			1160		nC
Q_{gc}	Gate – Collector Charge	$I_{\rm C} = 360 {\rm A}$		800			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 360A$ $R_{G} = 1.25\Omega$			26		ns
T_{r}	Rise Time				25		
$T_{d(off)}$	Turn-off Delay Time				150		
T_{f}	Fall Time				30		
$T_{d(on)}$	Turn-on Delay Time	Inductive Swit	ching (125°C)		26		
T_{r}	Rise Time	$\begin{aligned} V_{GE} &= 15V \\ V_{Bus} &= 400V \\ I_{C} &= 360A \\ R_{G} &= 1.25\Omega \end{aligned}$			25		ns
$T_{d(off)}$	Turn-off Delay Time				170		
T_{f}	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 125$ °C		17.2		mJ
E _{off}	Turn-off Switching Energy	$I_C = 360A$ $R_G = 1.25\Omega$	$T_j = 125$ °C		14		1117

Chopper diode ratings and characteristics

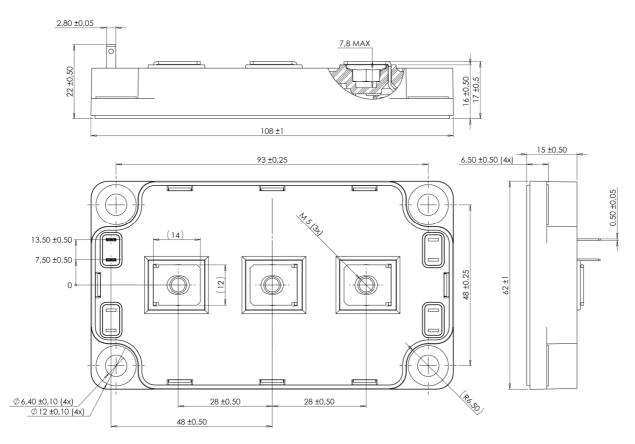
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
т	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$			750	۸
I_{RM}			$T_j = 125$ °C			1500	μΑ
I_F	DC Forward Current		Tc = 80°C		400		Α
	Diode Forward Voltage	$I_F = 400A$			1.6	1.8	
V_{F}		$I_F = 800A$			1.9		V
		$I_F = 400A$	$T_j = 125$ °C		1.4		
t _{rr}	Reverse Recovery Time	$ \begin{array}{c c} I_F = 400A & T_j = 12 \\ V_R = 400V & T_j = 12 \\ di/dt = 800A/\mu s & T_j = 25 \end{array} $	$T_j = 25^{\circ}C$		180		ns
			$T_{j} = 125^{\circ}C$		220		115
Q _{rr}	Reverse Recovery Charge		$T_j = 25$ °C		1560		пC
			$T_{j} = 125^{\circ}C$		5800		110



Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance IGBT Diode				0.08	°C/W	
			Diode			0.16	C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					300	g

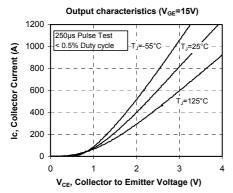
SP6 Package outline (dimensions in mm)

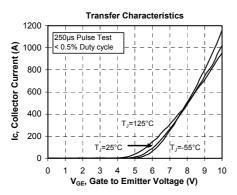


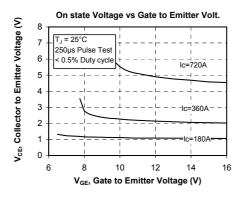
 $See \ application \ note \ APT0601 - Mounting \ Instructions \ for \ SP6 \ Power \ Modules \ on \ www.microsemi.com$

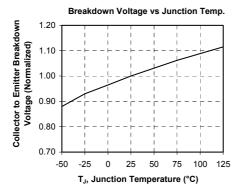


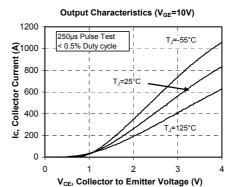
Typical Performance Curve

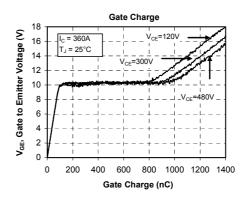


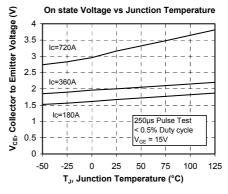


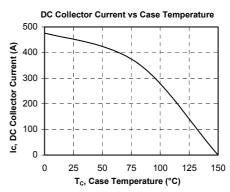




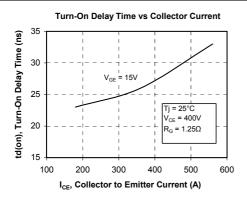


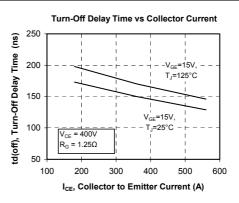


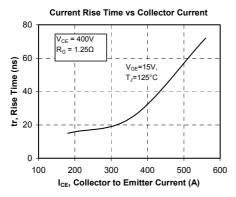


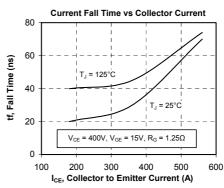


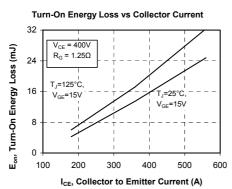


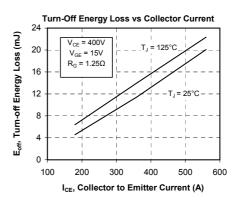


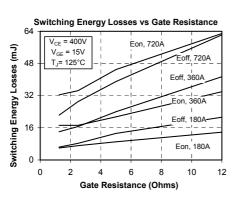




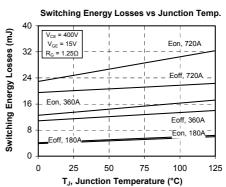




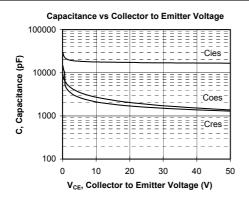


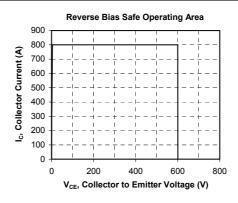


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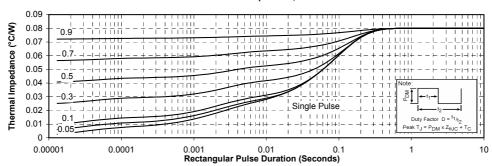


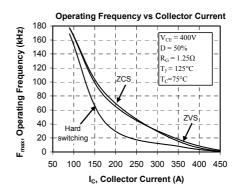






Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration







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